

ITR9904



Features

- Fast response time
- High analytic
- Cut-off visible wavelength $\lambda_c=940\text{nm}$
- High sensitivity
- This product itself will remain within RoHS compliant version.

Description

The ITR9904 consists of an infrared emitting diode and an NPN silicon phototransistor, encased oblique angle (45°) on converging optical axis in a black Thermo-plastic housing. The phototransistor receives radiation from the IRED only, and avoids the noise from ambient light.

Applications

- Copier
- Scanner
- Non-contact Switching
- For Direct PC Board

Device Selection Guide

Device No.	Chip Material
IR	GaAlAs
PT	Silicon

Absolute Maximum Ratings (Ta=25 °C)

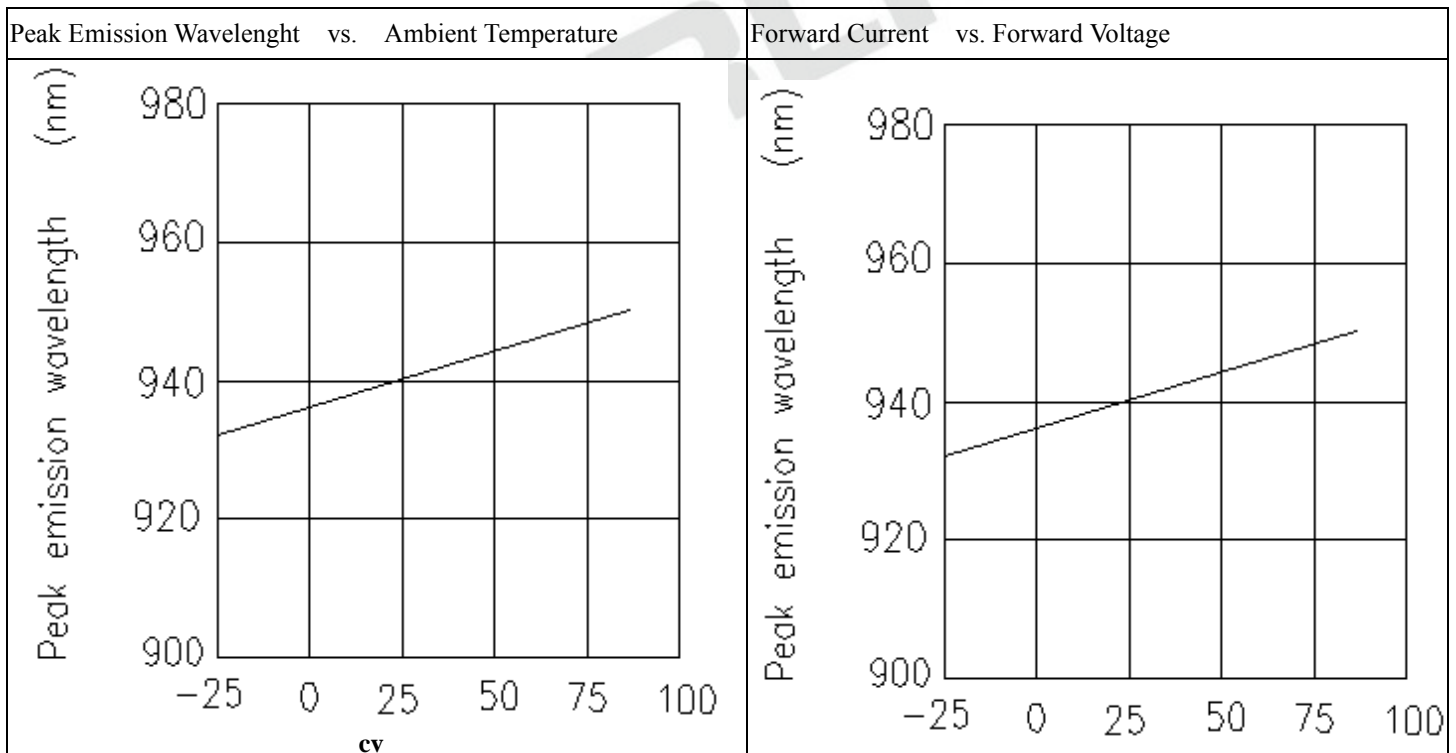
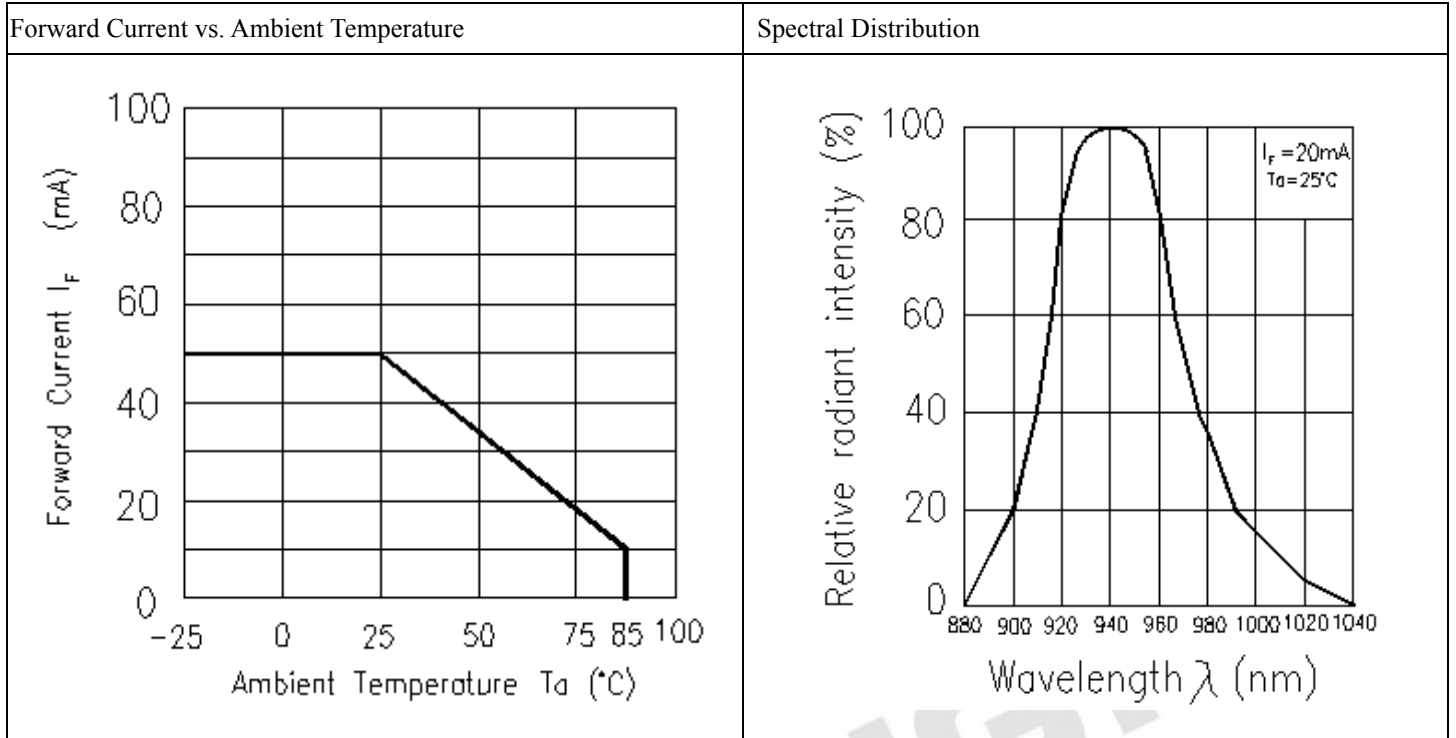
Parameter		Symbol	Ratings	Unit
Input	Power Dissipation at(or below) 25 °C Free Air Temperature	PD	75	mW
	Reverse Voltage	VR	5	V
	Forward Current	IF	50	mA
	Peak Forward Current (*1)	IFP	1.0	A
Output	Collector Power Dissipation	Pc	75	mW
	Collector Current	Ic	20	mA
	Collector-Emitter Voltage	VCE	30	V
	Emitter-Collector Voltage	VEC	5	V
Operating Temperature		Topr	-25~+85	
Storage Temperature		Tstg	-40~+85	
Lead Soldering Temperature (*2)		Tsol	260	

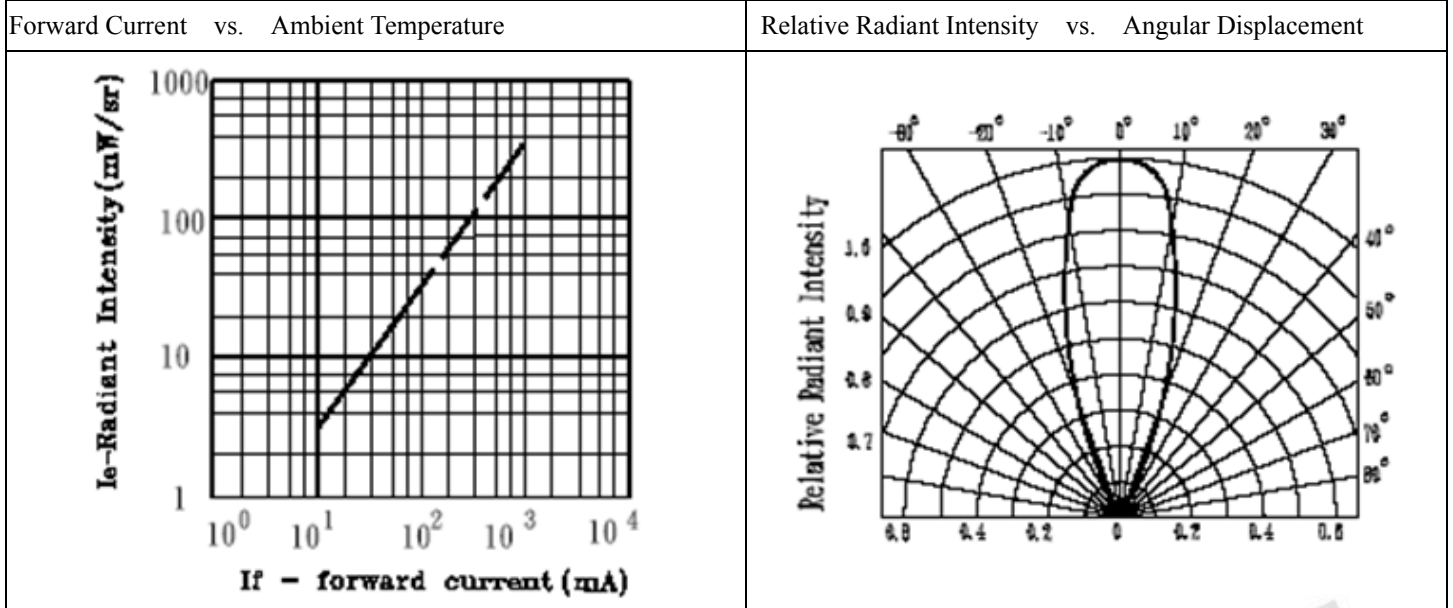
Notes: (*1) Pause width= 100 μs, Duty Cycle=1% (*2) t=5 secs

Electro-Optical Characteristics (Ta=25)

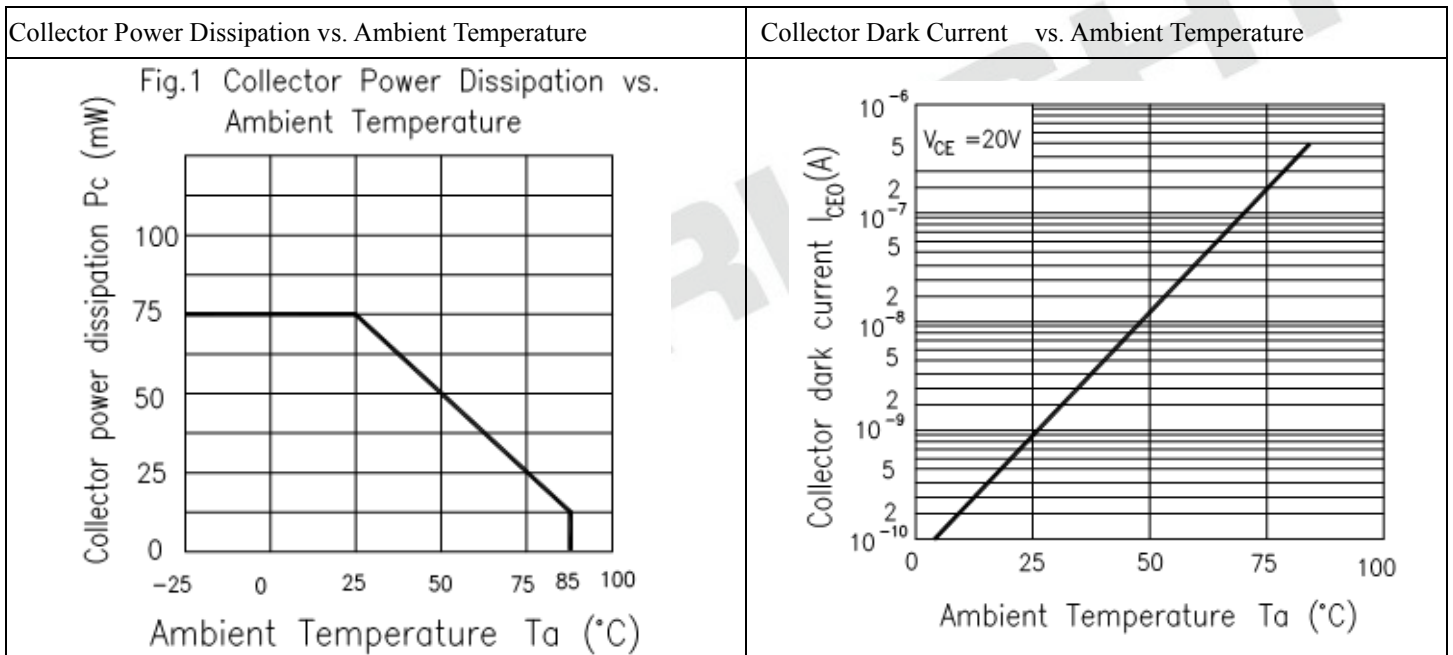
Parameter		Symbol	Min.	Typ.	Max.	Unit	Condition
Input	Forward Voltage	V _{F1}	-	1.2	1.5	V	I _F =20mA
		V _{F2}	-	1.4	1.85		I _F =100mA
		V _{F3}	-	2.6	4.0		I _F =1A
	Reverse Current	I _R	-	-	10	μA	V _R =5V
	Peak Wavelength	λ _p	-	940	-	nm	---
	View Angle	2θ _{1/2}	-	35	-	Deg	I _F =20mA
Output	Dark Current	I _{CEO}	-	-	100	nA	V _{CE} =20V, E _e =0mW/cm ²
	C-E Saturation Voltage	V _{CE(sat)}	-	-	0.4	V	I _C =2mA, I _B =0.1mA
Collect Current		I _{C(ON)A}	100	-	300	μA	V _{CE} =5V, I _F =20mA
		I _{C(ON)B}	200	-	600		
		I _{C(ON)C}	400	-	1200		
Response Time	Rise Time	t _R	-	15	-	μs	V _{CE} =2V, I _C =1mA, R _L =1KΩ
	Fall Time	t _F	-	15	-	μs	

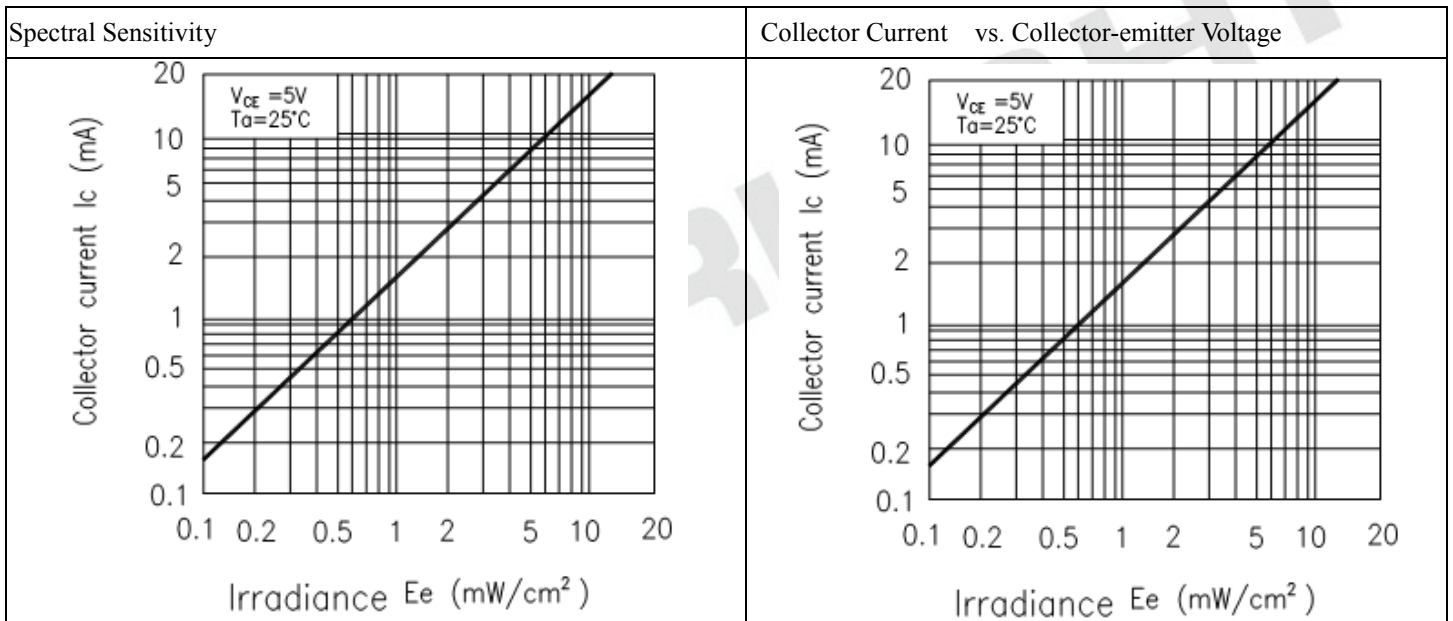
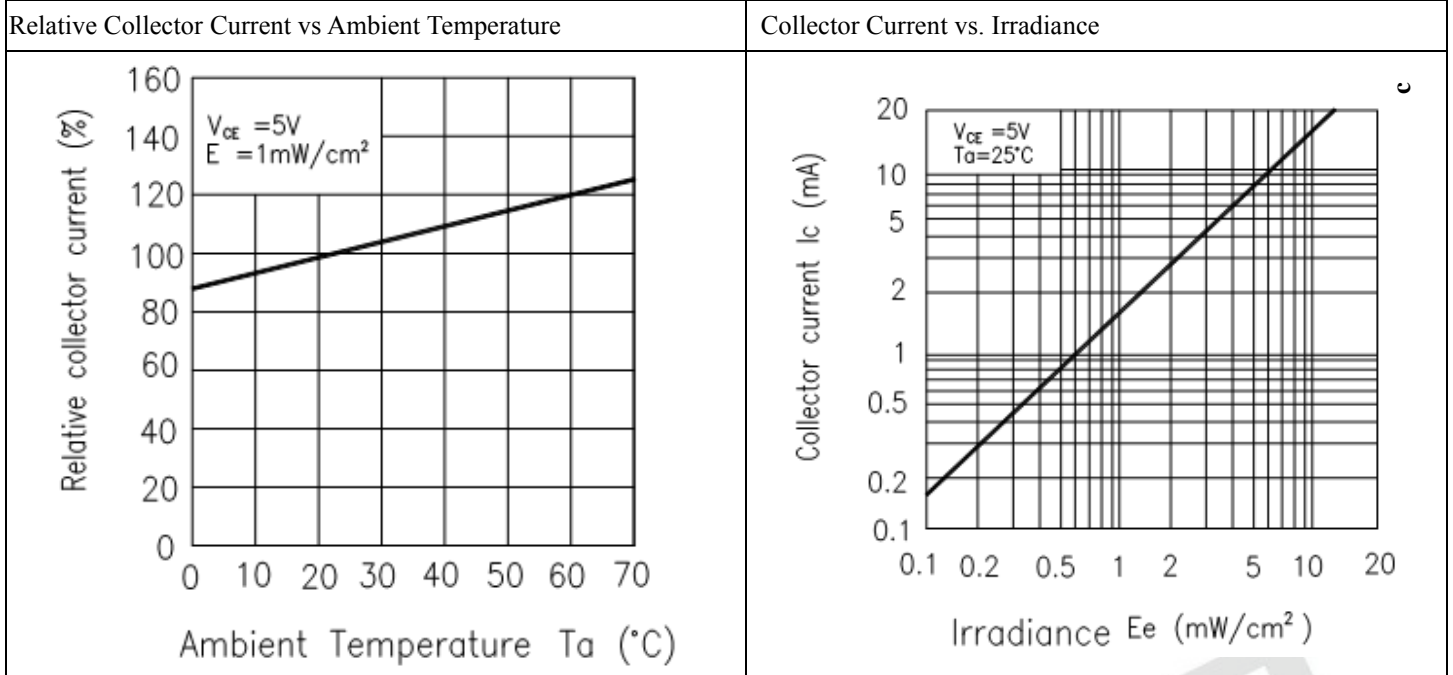
Typical Electrical/Optical/Characteristics Curves for IR



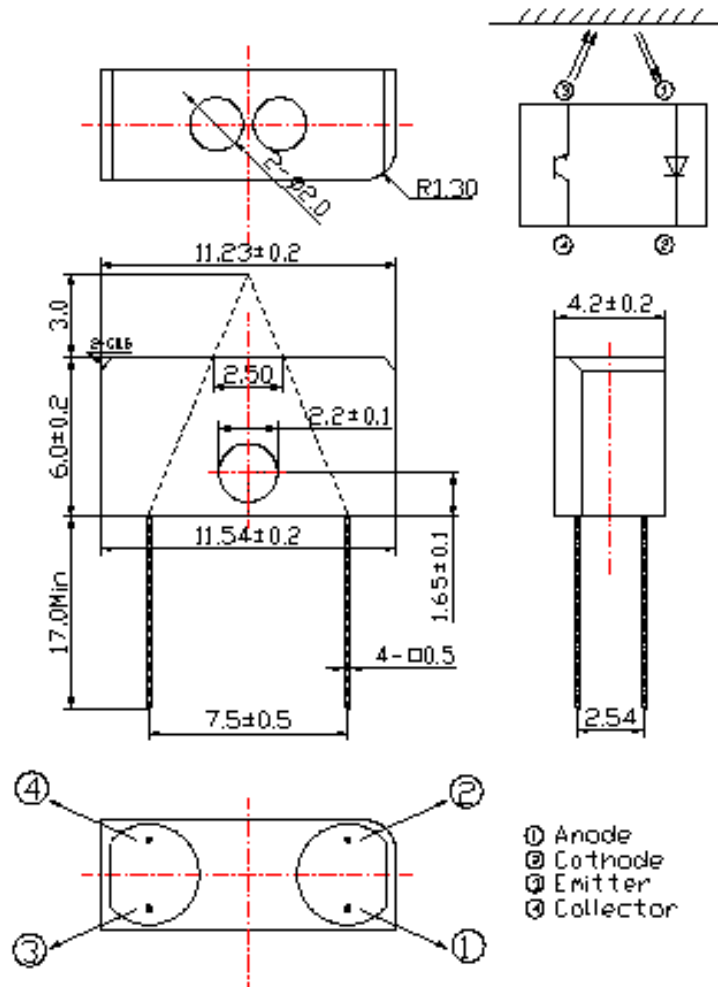


Typical Electro/Optical/Characteristics Curves for PT





Package Dimension



Notes:

1. All dimensions are in millimeter.
2. General tolerance: ± 0.2 mm
3. Lead spacing is measured where the lead emerge from the package.
4. Above specification may be changed without notice. EVERLIGHT will reserve authority on material change for above specification.
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Packing Quantity Specification

150 pcs/1bag , 5 bags/1box , 10 boxes/1carton

Label Form Specification



- CPN: Customer's Product Number
- P/N: Product Number
- QTY: Packing Quantity
- CAT: Luminous Intensity Rank
- HUE: Dom. Wavelength Rank
- REF: Forward Voltage Rank
- LOT No: Lot Number
- X: Month
- Reference: Identify Label Number

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